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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PRELIMINARY AMENDMENT ACCOMPANYING APPLICATION

APPLICANT: Etsuo Morita ATTY. DOCKET NO. 09792909-4715

SERIAL NO.

DATE FILED:

INVENTION: "METHOD OF MANUFACTURING CRYSTAL OF III-V
COMPOUND OF THE NITRIDE SYSTEM, CRYSTAL
SUBSTRATE OF III-V COMPOUND OF THE NITRIDE SYSTEM,
CRYSTAL FILM OF III-V COMPOUND OF THE NITRIDE
SYSTEM, AND METHOD OF MANUFACTURING DEVICE"

Assistant Commissioner of Patents
Washington, D.C. 20231

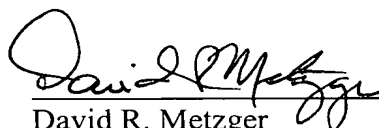
S I R:

Between the title and the heading "Background of the Invention" on page 1, insert the
following:

RELATED APPLICATION DATA

The present application claims priority to Japanese Application No. P11-345246 filed
December 3, 1999, which application is incorporated herein by reference to the extent
permitted by law.

Respectfully submitted,



(Reg. No. 32,919)

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